

Notice of Allowability	Application No.	Applicant(s)	
	09/490,502	ZHANG, HONGYUNG	
	Examiner Tai Duong	Art Unit 2871	

-- The MAILING DATE of this communication appears on the cover sheet with the correspondence address--

All claims being allowable, PROSECUTION ON THE MERITS IS (OR REMAINS) CLOSED in this application. If not included herewith (or previously mailed), a Notice of Allowance (PTO-85) or other appropriate communication will be mailed in due course. **THIS NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT RIGHTS.** This application is subject to withdrawal from issue at the initiative of the Office or upon petition by the applicant. See 37 CFR 1.313 and MPEP 1308.

1. This communication is responsive to Amendment 08/03/04.
2. The allowed claim(s) is/are 1-8 and 10-14.
3. The drawings filed on _____ are accepted by the Examiner.
4. Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).
 - a) All b) Some* c) None of the:
 1. Certified copies of the priority documents have been received.
 2. Certified copies of the priority documents have been received in Application No. _____.
 3. Copies of the certified copies of the priority documents have been received in this national stage application from the International Bureau (PCT Rule 17.2(a)).

* Certified copies not received: _____.

Applicant has THREE MONTHS FROM THE "MAILING DATE" of this communication to file a reply complying with the requirements noted below. Failure to timely comply will result in ABANDONMENT of this application.

THIS THREE-MONTH PERIOD IS NOT EXTENDABLE.

5. A SUBSTITUTE OATH OR DECLARATION must be submitted. Note the attached EXAMINER'S AMENDMENT or NOTICE OF INFORMAL PATENT APPLICATION (PTO-152) which gives reason(s) why the oath or declaration is deficient.
 6. CORRECTED DRAWINGS (as "replacement sheets") must be submitted.
 - (a) including changes required by the Notice of Draftsperson's Patent Drawing Review (PTO-948) attached
 - 1) hereto or 2) to Paper No./Mail Date 02/12/03.
 - (b) including changes required by the attached Examiner's Amendment / Comment or in the Office action of Paper No./Mail Date _____.
- Identifying indicia such as the application number (see 37 CFR 1.84(c)) should be written on the drawings in the front (not the back) of each sheet. Replacement sheet(s) should be labeled as such in the header according to 37 CFR 1.121(d).
7. DEPOSIT OF and/or INFORMATION about the deposit of BIOLOGICAL MATERIAL must be submitted. Note the attached Examiner's comment regarding REQUIREMENT FOR THE DEPOSIT OF BIOLOGICAL MATERIAL.

Attachment(s)

1. Notice of References Cited (PTO-892)
2. Notice of Draftsperson's Patent Drawing Review (PTO-948)
3. Information Disclosure Statements (PTO-1449 or PTO/SB/08),
Paper No./Mail Date _____
4. Examiner's Comment Regarding Requirement for Deposit
of Biological Material
5. Notice of Informal Patent Application (PTO-152)
6. Interview Summary (PTO-413),
Paper No./Mail Date _____.
7. Examiner's Amendment/Comment
8. Examiner's Statement of Reasons for Allowance
9. Other _____.

REASONS FOR ALLOWANCE

The following is an examiner's statement of reasons for allowance:

The rejections under 35 U.S. C. 112 of claims 3, 5, 7, 8, 12 and 13 are withdrawn in view of Applicant's remarks. See pages 11, 13 and 16-18 of the Remarks.

Claims 1-8 and 10-14 are allowed over the prior art of record.

Claim 1 is allowed because none of the prior art discloses or suggests the steps of performing arraying for plotting a master glass substrate into a plurality of blocks, further plotting each block into one, alternatively a plurality of device-forming regions, and forming a conductive film, an insulating film and a semiconductor film which constitute TFT (Thin Film Transistor) in the device-forming region; performing primary cutting for cutting the master glass substrate into the respective blocks to form a plurality of sub-TFT substrates; performing sub-TFT substrate processing for executing processing for each sub-TFT substrate in accordance with a device to be manufactured; and performing secondary cutting for cutting the sub-TFT substrate into each of the device-forming regions *in combination with* the step wherein the sub-TFT substrate processing step includes a step of forming a semiconductor film above the sub-TFT substrate.

Claim 4 is allowed because none of the prior art discloses or suggests the steps of performing arraying for plotting a master glass substrate into a plurality of blocks, further plotting each block into one, alternatively a plurality of device-forming regions, and forming a conductive film, an insulating film and a semiconductor film which constitute TFT (Thin Film Transistor) in the device-forming region; performing primary

cutting for cutting the master glass substrate into the respective blocks to form a plurality of sub-TFT substrates; performing sub-TFT substrate processing for executing processing for each sub-TFT substrate in accordance with a device to be manufactured; and performing secondary cutting for cutting the sub-TFT substrate into each of the device-forming regions *in combination with* the step wherein the sub-TFT substrate processing step includes the steps of: forming a pixel electrode above the sub-TFT substrate; forming an orientation film for covering the pixel electrode; and joining a second substrate onto the sub-TFT substrate, and after the secondary cutting step, a step of sealing a liquid crystal between the sub-TFT substrate and the second substrate after the cutting is provided.

Claim 8 is allowed because none of the prior art discloses or suggests the steps of performing arraying for plotting a master glass substrate into a plurality of blocks, further plotting each block into one, alternatively a plurality of device-forming regions, and forming a conductive film, an insulating film and a semiconductor film which constitute TFT (Thin Film Transistor) in the device-forming region; performing primary cutting for cutting the master glass substrate into the respective blocks to form a plurality of sub-TFT substrates; performing sub-TFT substrate processing for executing processing for each sub-TFT substrate in accordance with a device to be manufactured; and performing secondary cutting for cutting the sub-TFT substrate into each of the device-forming regions *in combination with* the step wherein the sub-TFT substrate processing step, alignment is performed providing a fiducial mark on each sub-TFT substrate.

The remaining claims are also allowed since they depend on the allowed claim 1.

Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

Any inquiry concerning this communication should be directed to Tai Duong at telephone number (571) 272-2291.

The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.



TVD

11/04


TOAN TON
PRIMARY EXAMINER